NPN 2N3441

SILICON POWER TRANSISTOR

The 2N3441 are NPN transistors mounted in TO-66 metal package with the collector connected to the case .
They are intended for use in general purpose switching and amplifier applications.
Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
V_{CEO}	Collector-Emitter Voltage	I_B = 0	140	V
V_{CBO}	Collector-Base Voltage	I_E = 0	160	V
V_{EBO}	Emitter-Base Voltage	I_C = 0	7	V
I_C	Collector Current		3	A
I_B	Base Current		2	A
P_t	Total Power Dissipation	@ T_C = 25°	25	W
T_J	Junction Temperature		200	°C
T_{Stg}	Storage Temperature		-65 to +200	°C

ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage (*)	I_C= 100 mA , I_B= 0 A	140	-	-	V
I_{CEO}	Collector Cutoff Current	V_{CE}= 140 V , I_B= 0	-	-	10	mA
I_{CEX}	Collector Cutoff Current	V_{CE}= 140 V , V_{BE}= 1.5 V	-	-	5	mA
		V_{CE}= 140 V , V_{BE}= 1.5 V T_{case} = 150°C	-	-	6	
I_{EBO}	Emitter Cutoff Current	V_{EB}= 7 V, I_C= 0 A	-	-	1	mA
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	I_C= 2.7 A , I_B= 900 mA	-	-	6	V
$V_{BE(on)}$	Base-Emitter on Voltage (*)	I_C= 40 A , I_B= 4 A	-	-	6.5	V
h_{FE}	DC Current Gain	I_C= 500 mA, V_{CE}= 4 V	25	-	100	-
		I_C= 2.7 A, V_{CE}= 4 V	5	-	-	

(*) Pulse Duration = 300 μs, Duty Cycle <= 1.5%

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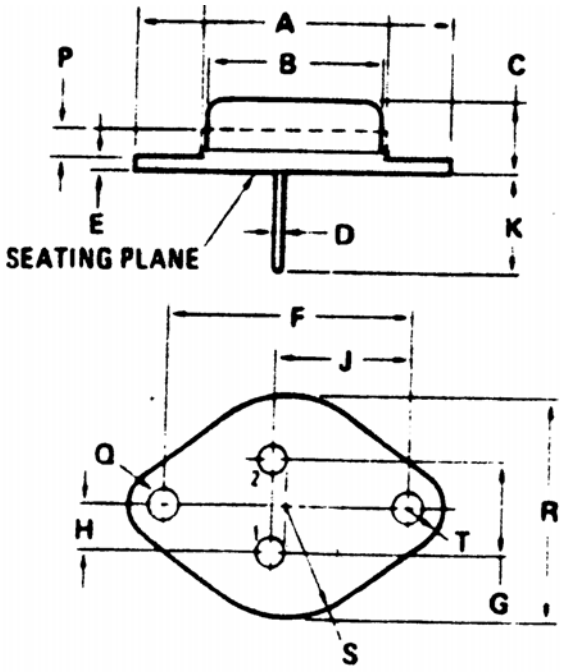
THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJC}	Thermal Resistance, Junction to Case	7	°C/W

MECHANICAL DATA CASE TO-66

DIMENSIONS		
	mm	
	min	max
A	30.60	32.52
B	11.94	12.7
C	6.35	8.63
D	0.712	0.863
E	1.27	1.91
F	24.28	24.50
G	4.83	5.33
H	2.41	2.67
J	14.48	14.99
K	9.15	10.50
P	-	2.7
Q	3.60	4.00
S	-	8.89
T	-	3.68



Pin 1 :	Emitter
Pin 2 :	Base
Case :	Collector

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